

自主封測 品質把控 售後保障

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電源管理



顯示驅動



二三極管



LDO穩壓器



觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

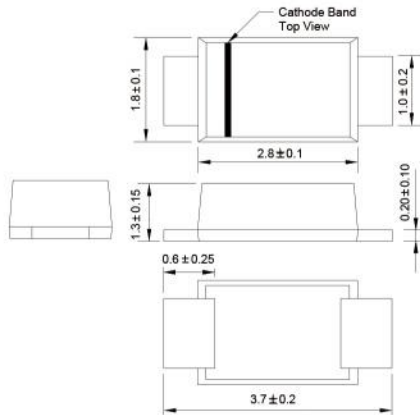
F1M-TD

產品規格說明書

SUFACE MOUNT FAST RECOVERY RECTIFIER

Reverse Voltage - 50 to 1000 Volts Forward Current - 1.0Ampere

SOD-123FL



Dimensions in millimeters

FEATURES

- ◆ Glass passivated device
- ◆ Ideal for surface mouted applications
- ◆ Low reverse leakage
- ◆ Metallurgically bonded construction
- ◆ High temperature soldering guaranteed:
250°C/10 seconds, 0.375" (9.5mm) lead length,
5 lbs. (2.3kg) tension

MECHANICAL DATA

Case : JEDEC SOD-123FL molded plastic body over passivated chip

Terminals : Plated axial leads, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight : 0.0007 ounce, 0.02 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 C ambieft temperature unless otherwise specified.
Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	F1A	F1B	F1D	F1G	F1J	F1K	F1M	UNITS
	MARK	F1A	F1B	F1D	F1G	F1J	F1K	F1M	
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at TA=65°C (NOTE 1)	I(AV)	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) TL=25°C	IFSM	20.0							Amps
Maximum instantaneous forward voltage at 1.0A	VF	1.3							Volts
Maximum DC reverse current TA=25°C at rated DC blocking voltage TA=125°C	IR	5.0 50.0							μA
Maximum reverse recovery time (NOTE 2)	trr	150				250	500		ns
Typical junction capacitance (NOTE 3)	CJ	4							pF
Typical thermal resistance (NOTE 4)	RθJA	180							K/W
Operating junction and storage temperature range	TJ TSTG	-55 to +150							°C

Note: 1. Averaged over any 20ms period.
2. Measured with $I_F=0.5\text{A}$, $I_R=1\text{A}$, $I_{rr}=0.25\text{A}$.
3. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
4. Thermal resistance junction to ambient, 6.0 mm² copper pads to each terminal.

FIG.1 –TYPICAL FORWARD CHARACTERISTIC

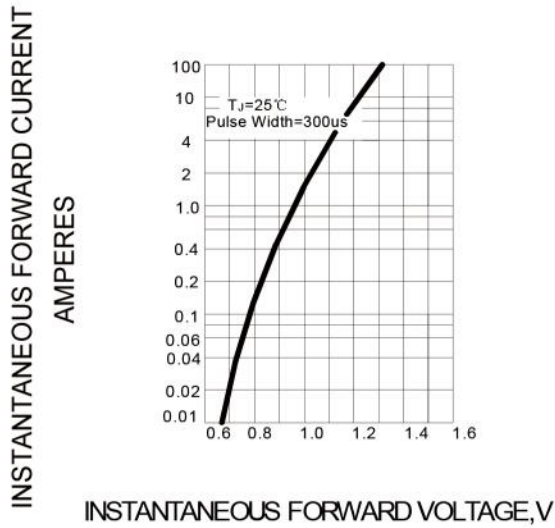


FIG.2 – TYPICAL JUNCTION CAPACITANCE

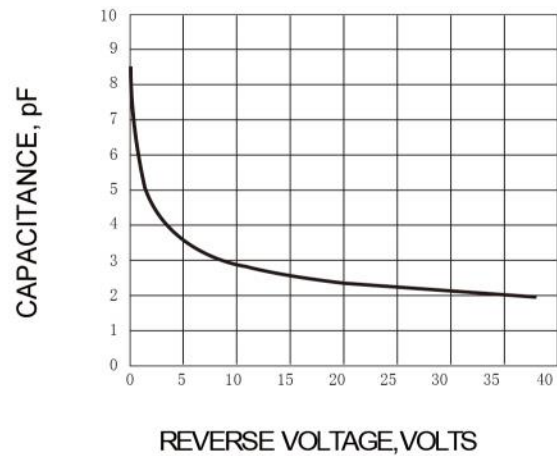


FIG.3 – TYPICAL INSTANTANEOUS REVERSE CHARACTERISTICS

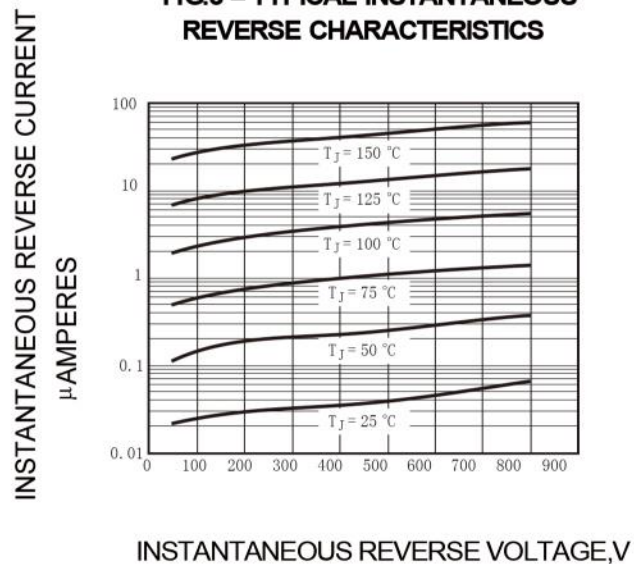


FIG.4 – FORWARD DERATING CURVE

